

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6805139") PN:	USPAT	OR	OFF	2005/04/20 13:43
L2	0	(alkaline adj stripper) and residue and (fluoride-free)	USPAT	OR	OFF	2005/04/20 13:44
L3	1	(alkaline adj stripper) and residue and (fluoride) and photoresist	USPAT	OR	OFF	2005/04/20 13:45
L4	593	(438/758).CCLS.	USPAT	OR	OFF	2005/04/20 13:45
L5	4	4 and stripper	USPAT	OR	OFF	2005/04/20 13:45
L6	453	(438/906).CCLS.	USPAT	OR	OFF	2005/04/20 13:45
L7	1	6 and (alkaline adj stripper)	USPAT	OR	OFF	2005/04/20 13:45
S1	368	(438/689).CCLS.	USPAT	OR	OFF	2005/04/20 12:57
S2	0	S1 and (alkaline adj stripper)	USPAT	OR	OFF	2004/12/09 14:05
S3	25	S1 and (alkaline)	USPAT	OR	OFF	2004/12/09 14:07
S4	7	S1 and (alkaline) and (silicon adj oxide)	USPAT	OR	OFF	2004/12/09 16:03
S5	383	SiOC	USPAT	OR	OFF	2004/12/09 16:03
S6	0	SiOC and (alkaline adj etchant)	USPAT	OR	OFF	2004/12/09 16:03
S7	278	(alkaline adj etchant)	USPAT	OR	OFF	2004/12/09 16:03
S8	43	(alkaline adj etchant) and insulating and dielectric	USPAT	OR	OFF	2004/12/09 16:05
S9	6	(alkaline adj etchant) and insulating and (low adj dielectric)	USPAT	OR	OFF	2004/12/09 16:11
S10	2	SiOC and copper and amine and etchant	USPAT	OR	OFF	2004/12/14 14:46
S11	2	SiOC and copper and amine and etchant and mask	USPAT	OR	OFF	2004/12/14 15:17
S12	603	(134/1.3).CCLS.	USPAT	OR	OFF	2004/12/14 15:17
S13	208	S12 and rinse	USPAT	OR	OFF	2004/12/14 15:17
S14	24	S12 and etch and ash	USPAT	OR	OFF	2004/12/14 15:17
S15	153	amine and etch and ash and pH	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
S16	723	photoresist and mask and etch and ash	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
S17	326	photoresist and mask and etch and ash and copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18

S18	145	photoresist and mask and etch and ash and copper and residue	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
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